

In the Specification:

Please amend the specification as follows:

Page 1, first paragraph:

CROSS-REFERENCE TO RELATED APPLICATIONS

The present invention claims priority from Finnish patent application 20030919 filed 19 June 2003 and is the National Phase application under 35 U.S.C. § 371 of PCT/FI2004/050098.

Field of the invention

The invention relates to a method for manufacturing an electronic thin-film component, ~~according to the preamble of the appended independent claim 1. The invention also relates to an apparatus implementing the method, and according to the preamble of the appended claim 15. Furthermore, the invention relates to an electronic thin-film component according to the appended independent claim 24.~~

Page 5, first full paragraph:

~~To attain these purposes, the method according to the invention for manufacturing a thin film component is primarily characterized in what is presented in the characterizing part of the~~

~~appended independent claim 1. The apparatus according to the invention, in turn, is primarily characterized in what will be presented in the characterizing part of the appended independent claim 15. The thin film component according to the invention is primarily characterized in what will be presented in the characterizing part of the appended independent claim 24. The other, dependent claims will present some advantageous embodiments of the invention.~~

Paragraph bridging pages 13 and 14:

In view of the present invention, an essential aspect in producing a master element necessary in the manufacture of the pressing block is that the method is capable of replicating certain properties of the pressing block, of which the most important ones include the vertical orientation of the walls of the relief, and the quality of the edges of the relief. Thus, the manufacturing method should be selected so that it is optimal for each separate pattern geometry. Direct laser lithography may be used for line widths of  $>1.5$   $\mu\text{m}$  and line widths smaller than this are typically produced by means of an electron beam. Another essential aspect in view of the invention is the depth of the lines in the relief. It is known that for example the line width of 25  $\mu\text{m}$  and depth 50  $\mu\text{m}$  can be produced with a nearly vertical wall by optimizing the exposure and development process of the resists accurately. However, in most cases it is easier to use the above-described dry etching process by means of which it is possible to produce nearly completely vertical walls.